



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	62mΩ @ V _{GS} = -4.5V	-3.8A
-20V	90mΩ @ V _{GS} = -2.5V	-3.1A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

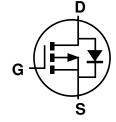
Features and Benefits

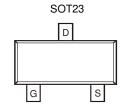
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)







Top View

Internal Schematic

Top View

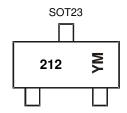
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2120U-7	SOT23	3,000/Tape & Reel
DMP2120U-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



212 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: H = 2020) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2017	^	,	2020	20	021	2022		2023	2024		2025
Code	Е	`	,	Н			J		K	┙		М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Ι _D	-3.8 -3.0	А		
Maximum Continuous Body Diode Forward Curr	ent (Note 6	6)	Is	-1.3	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)	•	I _{DM}	-20	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	0.8	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	163	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	114	G/ VV	
Total Power Dissipation (Note 6)		P_{D}	1.3	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	94	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	66	G/VV	
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

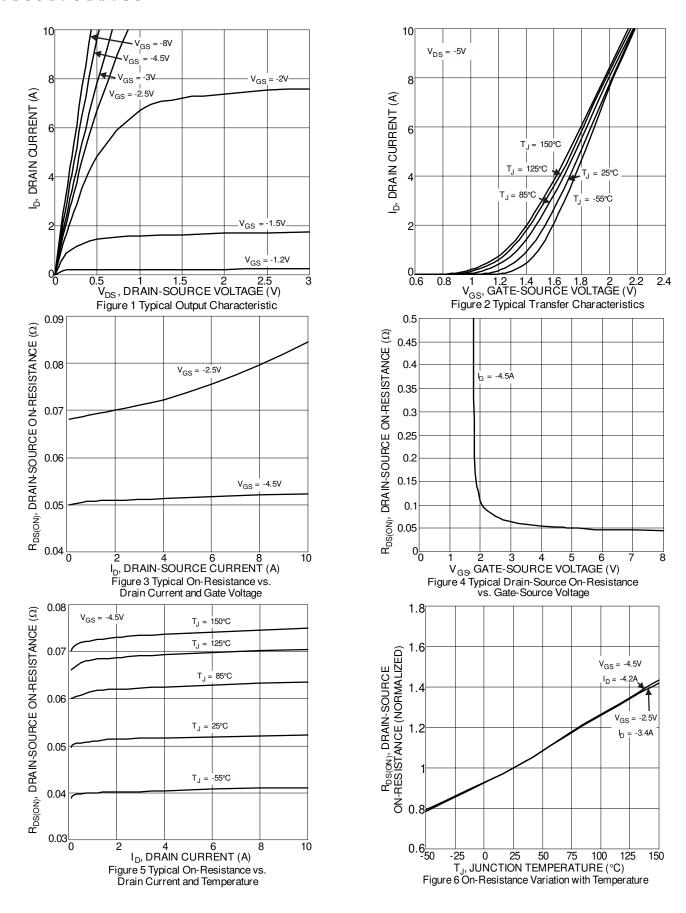
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		_	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-0.4	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			51	62		VGS = -4.5V, ID = -4.2A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	71	90	mΩ	$V_{GS} = -2.5V$, $I_{D} = -3.4A$	
	, ,		116	150		VGS = -1.8V, $ID = -2.0A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		487		pF	V 00V V 0V	
Output Capacitance	Coss		60	_	pF	$V_{DS} = -20V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		53	_	рF	1 = 1.0MH2	
Gate Resistance	R_{G}		39	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_{G}	_	6.3	_	nC	V 45V V 4V	
Gate-Source Charge	Q _{GS}		0.7	_	nC	$V_{GS} = -4.5V, V_{DS} = -4V,$	
Gate-Drain Charge	Q_{GD}		1.4	_	nC	$I_D = -3.5A$	
Turn-On Delay Time	t _{D(ON)}	_	5.3	_	ns		
Turn-On Rise Time	t _R		15.7	_	ns	$V_{DS} = -4V$, $V_{GS} = -4.5V$,	
Turn-Off Delay Time	t _{D(OFF)}		38.5	_	ns	$I_D = -1.0A, R_G = 6\Omega$	
Turn-Off Fall Time	t _F		23.2	_	ns]	
Body Diode Reverse Recovery Time	t _{RR}		7.5	_	ns	$I_S = -2.0A$, di/dt = -100A/ μ s	
Body Diode Reverse Recovery Charge	Q _{RR}	_	1.9	_	nC	$I_S = -2.0A$, $di/dt = -100A/\mu s$	

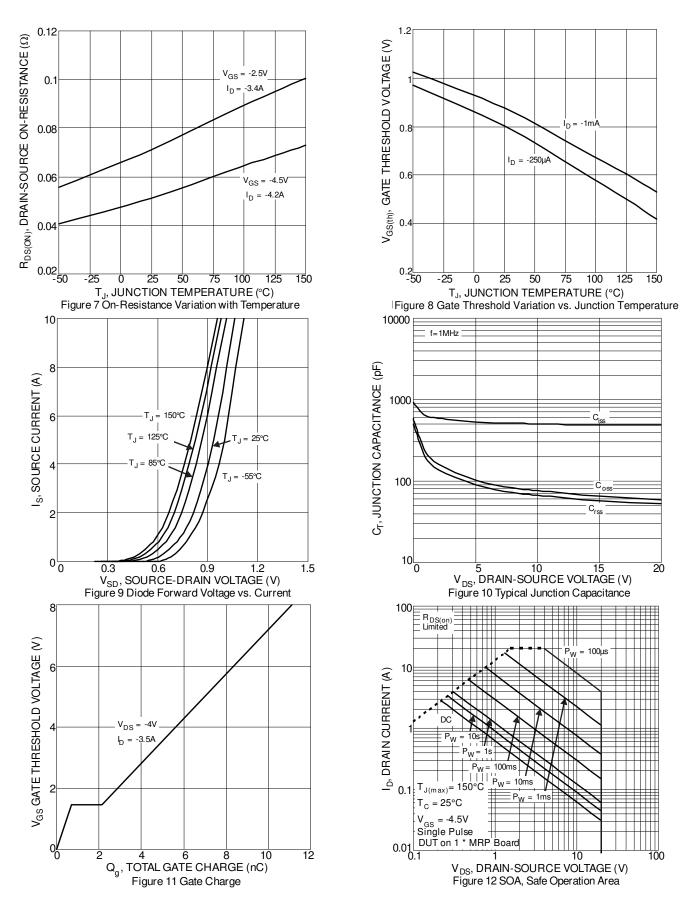
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Solution in the district of States (2004). Support, with 1 inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

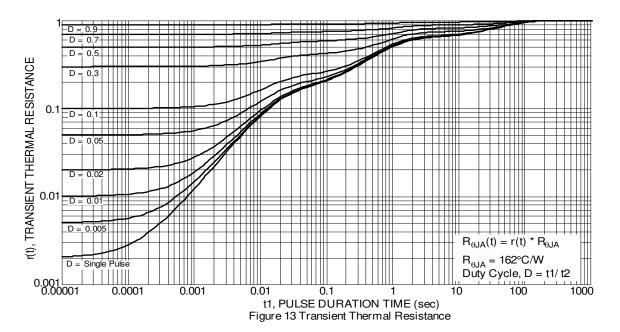








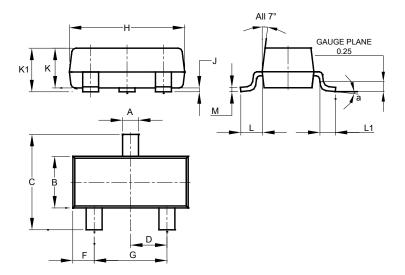






Package Outline Dimensions

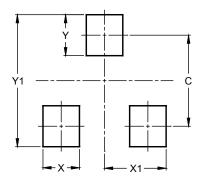
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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